

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \text{ max}}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
60V	80m Ω @ $V_{GS} = 10V$	4.1A
	100m Ω @ $V_{GS} = 4.5V$	3.6A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

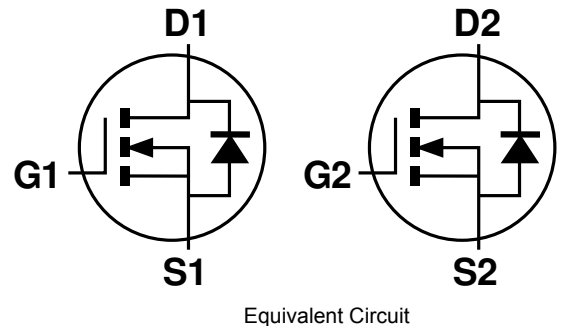
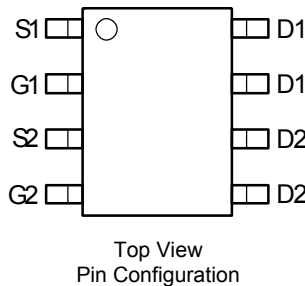
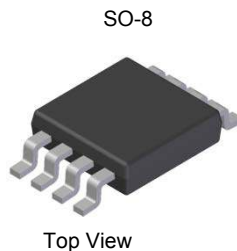
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (Approximate)

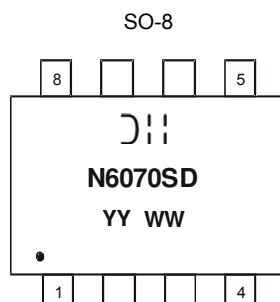


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6070SSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



$\text{D}::\text{I}$ = Manufacturer's Marking
 N6070SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	3.3
		$T_A = +70^\circ\text{C}$	2.6
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$	4.1
		$T_A = +70^\circ\text{C}$	3.4
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	2.0	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	12	A
Avalanche Current (Note 7) $L=0.1\text{mH}$	I_{AS}	10	A
Avalanche Energy (Note 7) $L=0.1\text{mH}$	E_{AS}	5.9	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		104
		$t < 10\text{s}$	61
Total Power Dissipation (Note 6)	P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		83
		$t < 10\text{s}$	50
Thermal Resistance, Junction to Case	$R_{\theta JC}$	14.5	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	68	80	m Ω	$V_{GS} = 10\text{V}, I_D = 4.5\text{A}$
			70	100		$V_{GS} = 4.5\text{V}, I_D = 3.5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1.1	V	$I_S = 12\text{A}, V_{GS} = 0\text{V}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	588	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	26.5	—		
Reverse Transfer Capacitance	C_{rss}	—	20	—		
Gate Resistance	R_g	—	1.5	—	Ω	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	5.6	—	nC	$V_{DS} = 30\text{V}, I_D = 3\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	12.3	—		
Gate-Source Charge	Q_{gs}	—	1.7	—		
Gate-Drain Charge	Q_{gd}	—	1.9	—		
Turn-On Delay Time	$t_{D(on)}$	—	3.5	—	nS	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}$ $R_L \cong 50\Omega, R_G \cong 20\Omega$
Turn-On Rise Time	t_r	—	4.1	—		
Turn-Off Delay Time	$t_{D(off)}$	—	35	—		
Turn-Off Fall Time	t_f	—	11	—		
Body Diode Reverse Recovery Time	t_{rr}	—	18	—	nS	$I_S = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{rr}	—	12	—	nC	$I_S = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

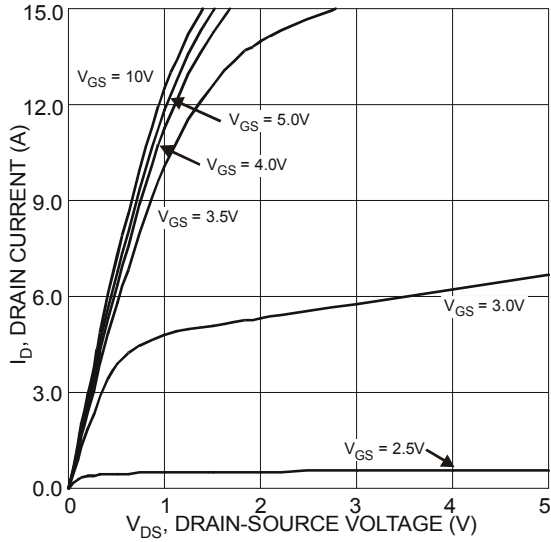


Figure 1 Typical Output Characteristic

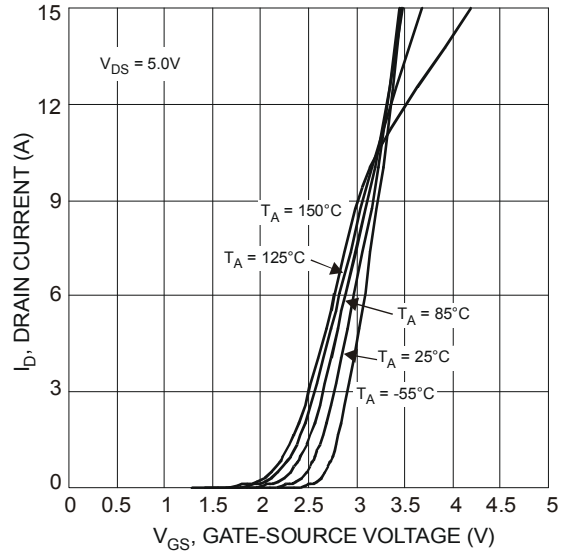


Figure 2 Typical Transfer Characteristics

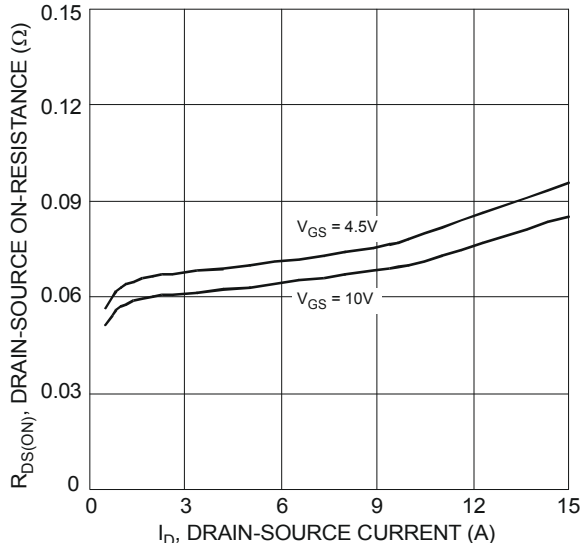


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

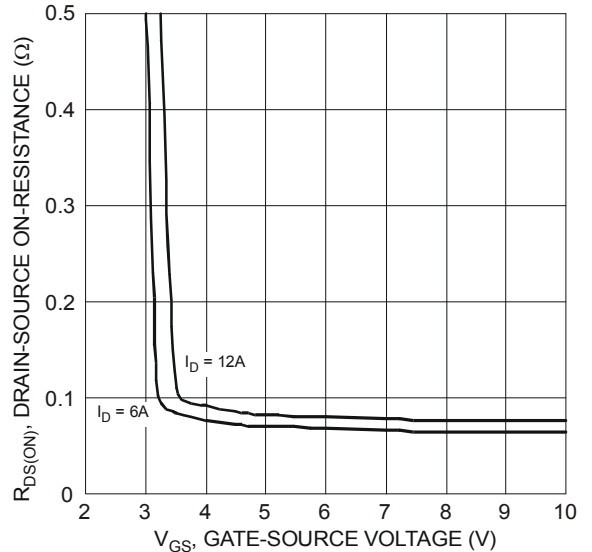


Figure 4 Typical Transfer Characteristics

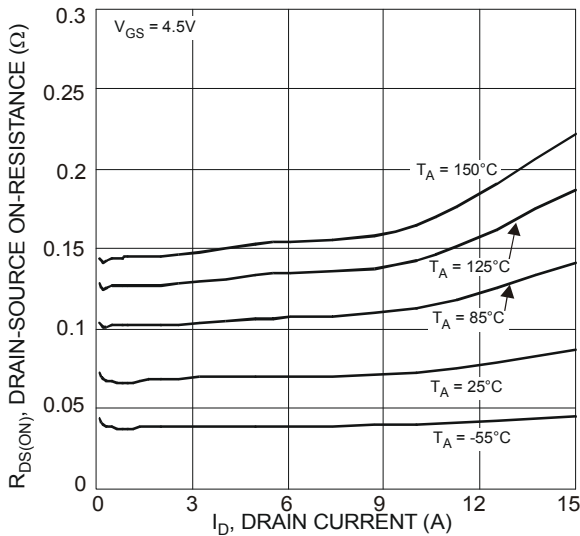


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

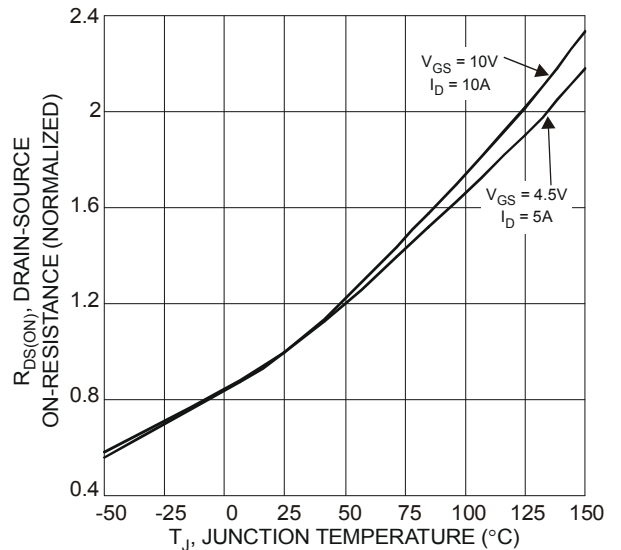


Figure 6 On-Resistance Variation with Temperature

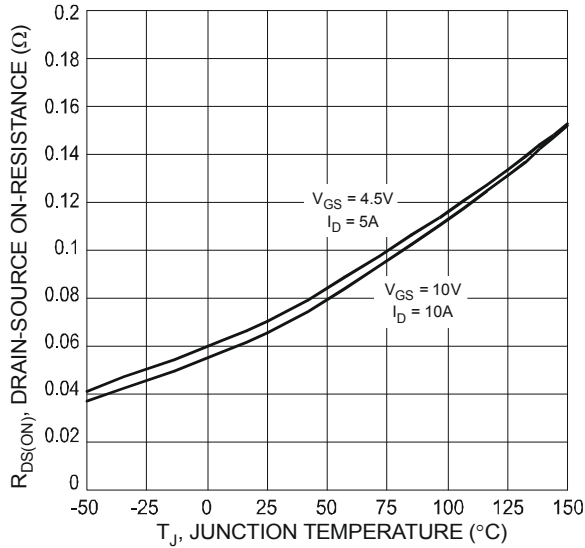


Figure 7 On-Resistance Variation with Temperature

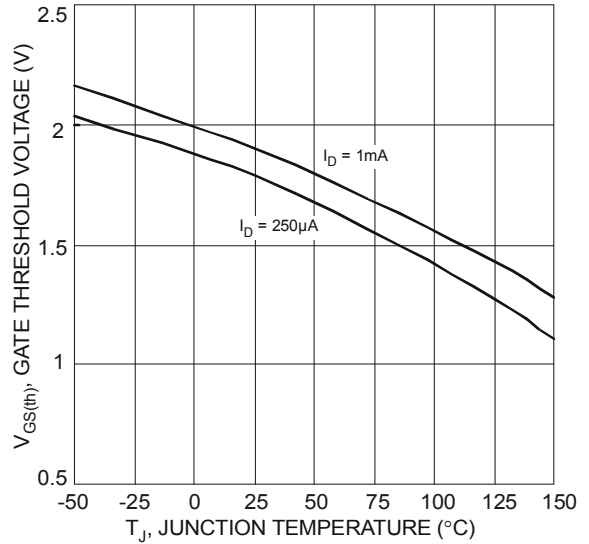


Figure 8 Gate Threshold Variation vs. Ambient Temperature

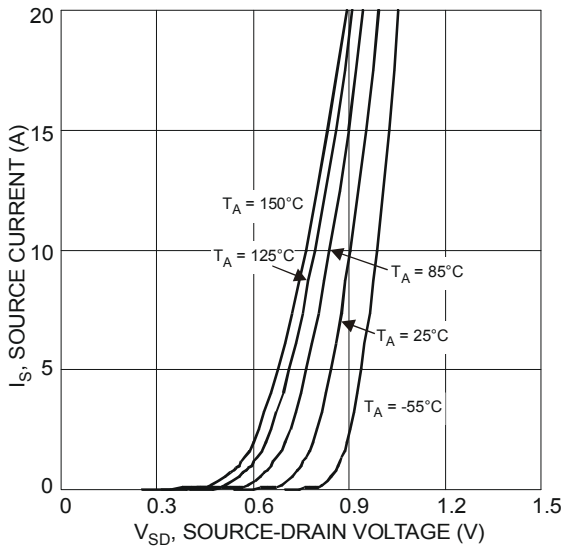


Figure 9 Diode Forward Voltage vs. Current

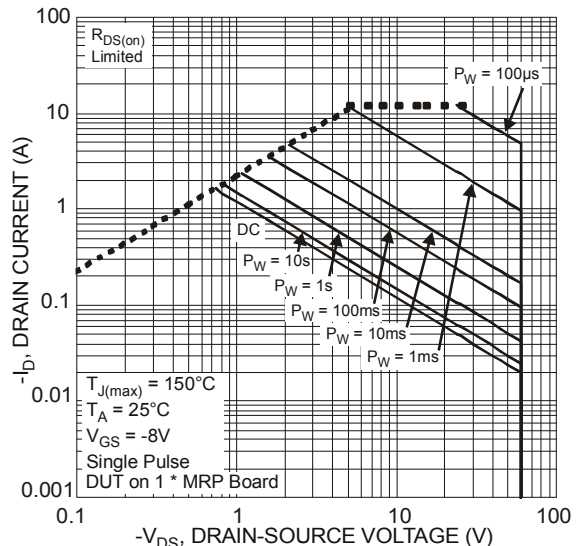


Figure 10 SOA, Safe Operation Area

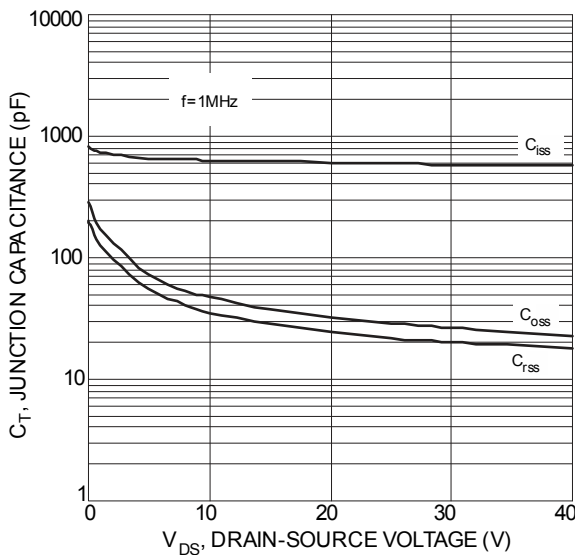


Figure 11 Typical Junction Capacitance

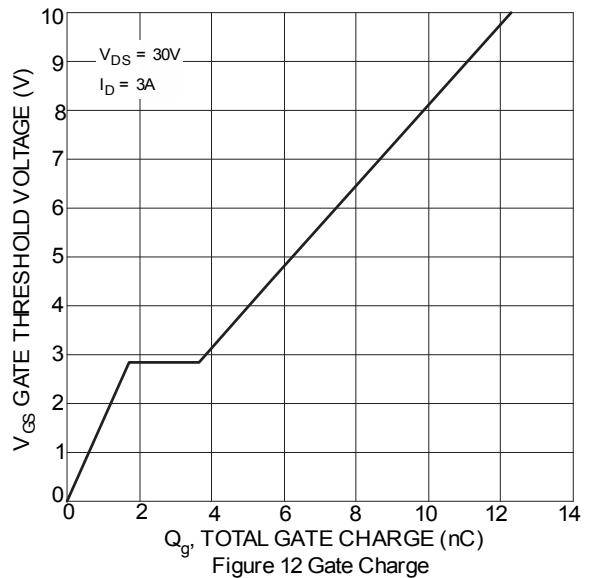
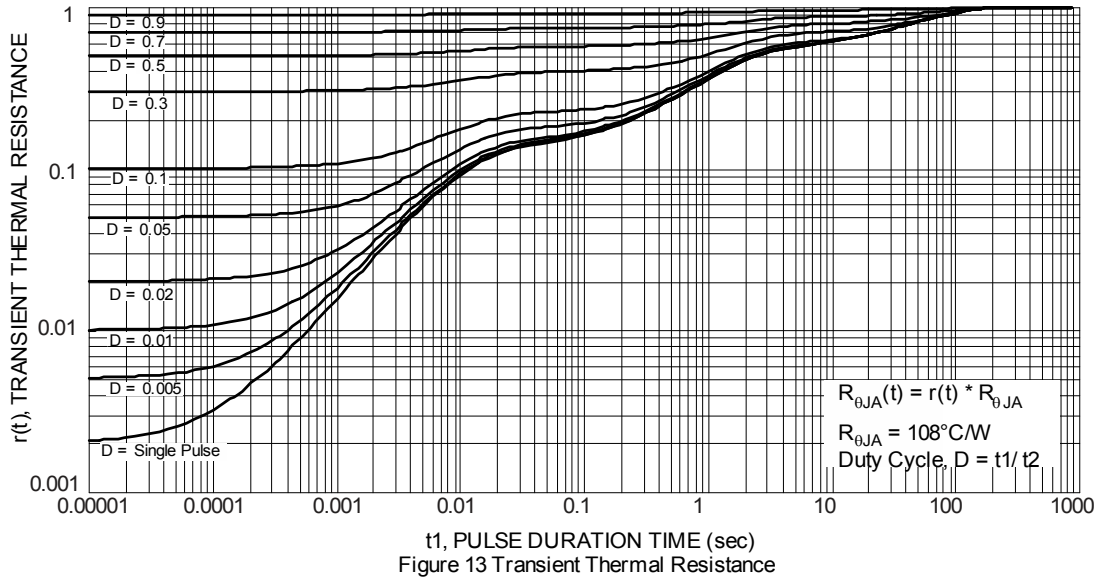
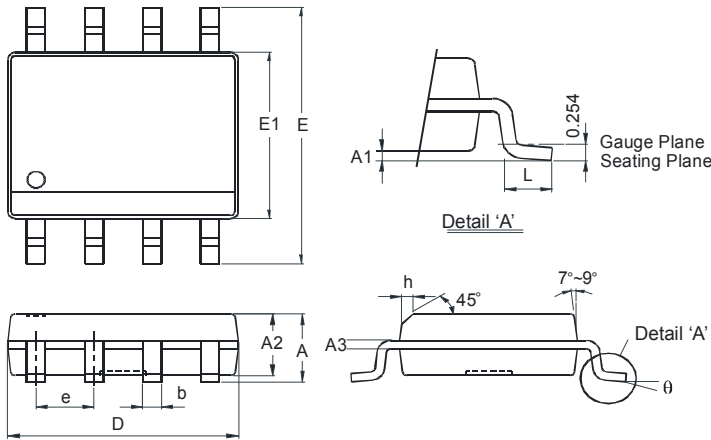


Figure 12 Gate Charge



Package Outline Dimensions

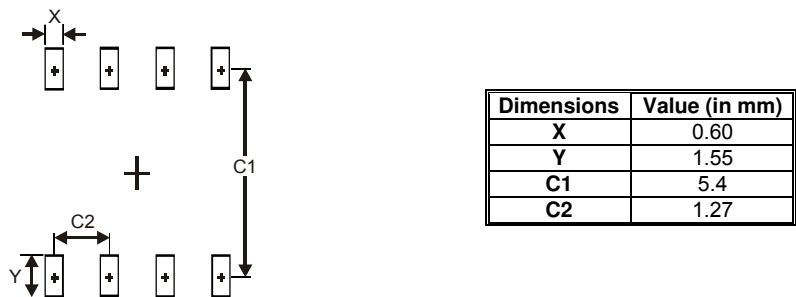
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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